

**IN THE CLAIMS:**

Please amend claim 19 as follows:

19. (Amended) A process according to claim 12, wherein stage a) comprises:

- delimiting the active zone according to a field oxidation (LOCOS) or shallow trench isolation technique, and
- doping the active area so as to give it the first conductivity type.

Please amend claim 20 as follows:

20. (Amended) A process according to claim 12, wherein the formation of the conductive layer (180) is preceded by the formation of lateral spacers (181) on the gates.

Please amend claim 21 as follows:

21. (Amended) A process according to claim 12, wherein the conductive layer (180) is a layer of silicide.

**PLEASE ADD THE FOLLOWING CLAIMS:**

22. A process according to claim 15, wherein stage a) comprises:

- delimiting the active zone according to a field oxidation (LOCOS) or shallow trench isolation technique, and
- doping the active area so as to give it the first conductivity type.

23. A process according to claim 15, wherein the formation of the conductive layer (180) is preceded by the formation of lateral spacers (181) on the gates.

24. A process according to claim 15, wherein the conductive layer (180) is a layer of silicide.